ASDM65S260NKQ

650V N-Channel Super-Junction MOSFET

Features

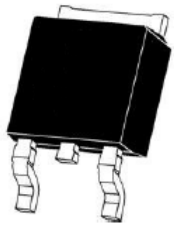
- Super-Junction MOSFET
- Low ON Resistance
- Improved dv/dt Capability
- 100% Avalanche Tested
- RoHS compliant

Product Summary

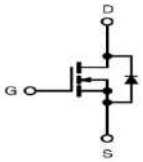
V_{DS}	650	V
$R_{DS(on),TYP}$@ V_{GS}=10 V	214	mΩ
I_D	16	A

Applications

- Switching Mode Power Supplies (SMPS)
- PWM Motor Controls
- LED Lighting
- Adapter



TO-252-2L top view



Schematic diagram

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain to Source Voltage	V_{DSS}	650	V
Continuous Drain Current (@T_C=25°C)	I_D	16 (1)	A
Continuous Drain Current (@T_C=100°C)		9 (1)	A
Drain current pulsed (2)	I_{DM}	45 (1)	A
Gate to Source Voltage	V_{GS}	±30	V
Single pulsed Avalanche Energy (3)	E_{AS}	270	mJ
MOSFET dv/dt Ruggedness(V_{DS}=0~400V)	dv/dt	40	V/ns
Peak diode Recovery dv/dt (4)	dv/dt	15	V/ns
Total power dissipation (@T_C=25°C)	P_D	52	W
Derating Factor above 25°C		0.41	W/°C
Operating Junction Temperature & Storage Temperature	T_{STG}, T_J	-55 to + 150	°C
Maximum lead temperature for soldering purpose	T_L	260	°C

Notes

1. Drain current is limited by maximum junction temperature.
2. Repetitive rating : pulse width limited by junction temperature.
3. L = 60mH, I_{AS} = 3A, V_{DD} = 50V, R_G=25Ω, Starting at T_J = 25°C
4. I_{SD} ≤ I_D, di/dt = 100A/us, V_{DD} ≤ 400V, Starting at T_J =25°C

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal resistance, Junction to case	R_{thjc}	2.4	°C/W
Thermal resistance, Junction to ambient	R_{thja}	67	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise specified)						
Parameter	**Symbol**	**Test conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Off Characteristics						
Drain to source breakdown voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	650	--	--	V
Breakdown voltage temperature coefficient	ΔBV_{DSS} / ΔTJ	I_D=250uA, referenced to 25°C	--	0.7	--	V/°C
Drain to source leakage current	I_{DSS}	V_{DS}=650V, V_{GS}=0V	--	--	1	uA
		V_{DS}=520V, T_C=125°C	--	--	10	uA
Gate to source leakage current, forward	I_{GSS}	V_{GS}=30V, V_{DS}=0V	--	--	100	nA
Gate to source leakage current, reverse		V_{GS}=-30V, V_{DS}=0V	--	--	-100	nA
On Characteristics						
Gate threshold voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250uA	2.0	3.3	4.0	V
Drain to source on state resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=7.5A	--	214	260	mΩ
Forward Transconductance	Gfs	V_{DS}=10V, I_D=7.5A	--	13.5	--	S
Dynamic Characteristics						
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=100V, f=1MHz	--	1299	--	pF
Output capacitance	C_{oss}		--	61	--	
Reverse transfer capacitance	C_{rss}		--	1	--	
Turn on delay time	$t_{d(on)}$	V_{DS}=325V, I_D=15A , R_G=25Ω,V_{GS}=10V	--	25	--	ns
Rising time	tr		--	34.5	--	
Turn off delay time	$t_{d(off)}$		--	107	--	
Fall time	t_f		--	28	--	
Total gate charge	Q_g	V_{DS}=325V, V_{GS}=10V, I_D=15A	--	25.2	--	nC
Gate-source charge	Q_{gs}		--	5.9	--	
Gate-drain charge	Q_{gd}		--	9.7	--	
Gate Resistance	Rg	V_{DS}=0V, Scan F mode	--	11	--	Ω

SOURCE TO DRAIN DIODE RATINGS CHARACTERISTICS						
Parameter	**Symbol**	**Test conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Continuous source current	I_S	Integral reverse p-n Junction diode in the MOSFET	--	--	16	A
Pulsed source current	I_{SM}		--	--	45	A
Diode forward voltage drop.	V_{SD}	I_S=16A, V_{GS}=0V	--	0.9	1.3	V
Reverse recovery time	T_{rr}	I_S=16A, V_{GS}=0V, dI_F/dt=100A/us	--	260	--	ns
Reverse recovery Charge	Qrr		--	3.5	--	uC

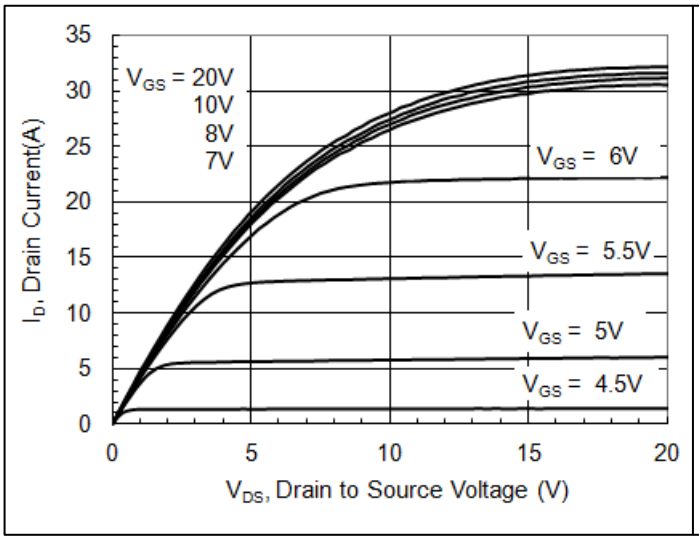


Fig1. Output characteristics

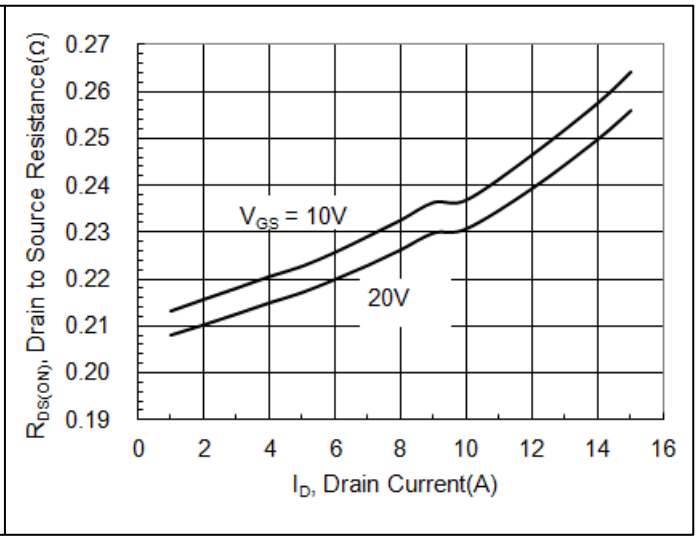


Fig2. Drain-source on-state resistance

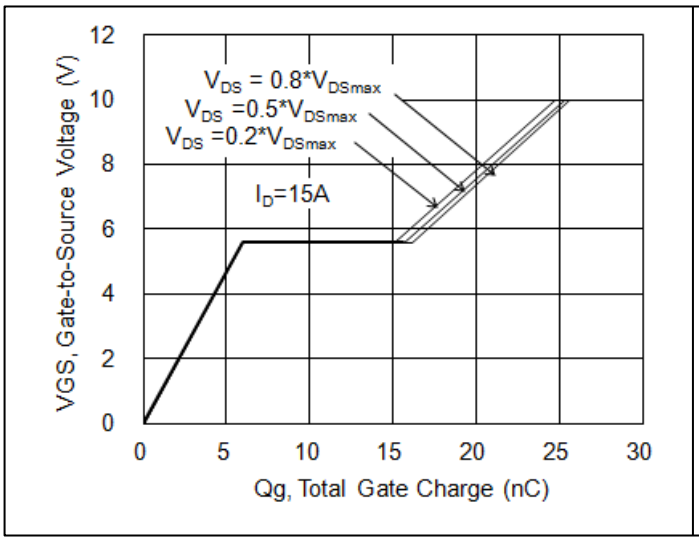


Fig3. Gate charge characteristics

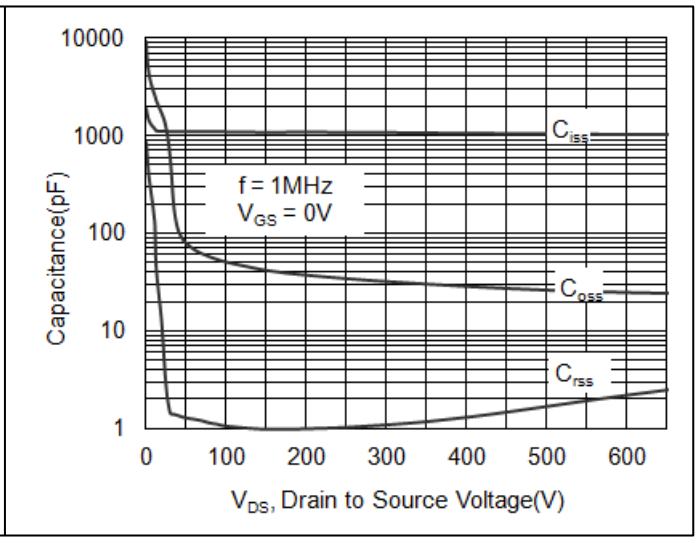


Fig 4. Capacitance Characteristics

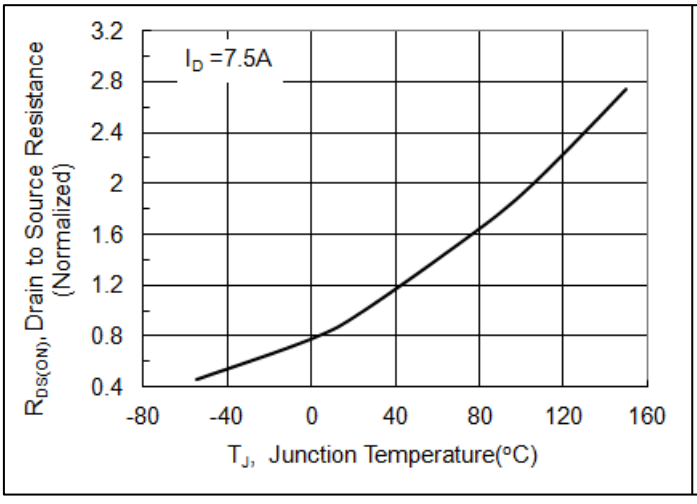


Fig 5. $R_{DS(ON)}$ vs junction temperature

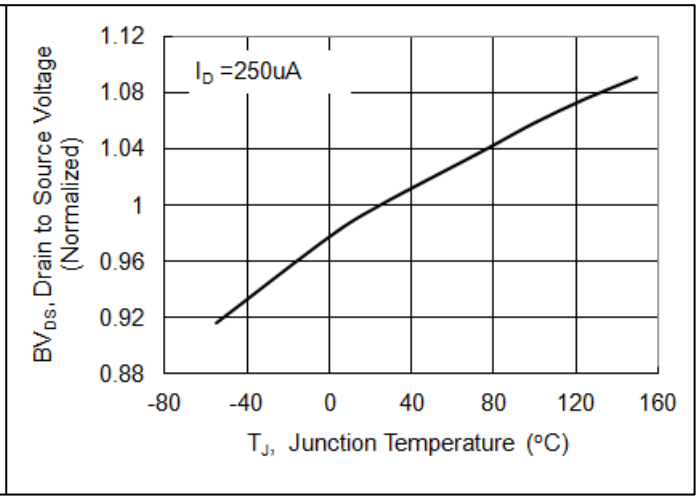


Fig 6. BV_{DSS} vs junction temperature

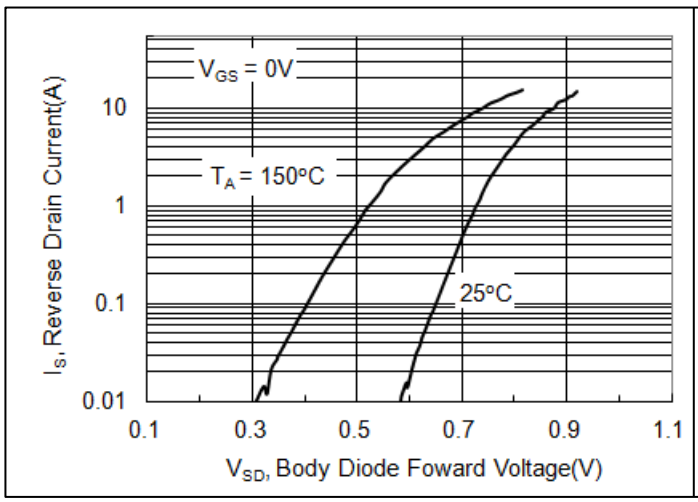


Fig 7 . Forward characteristics of reverse diode

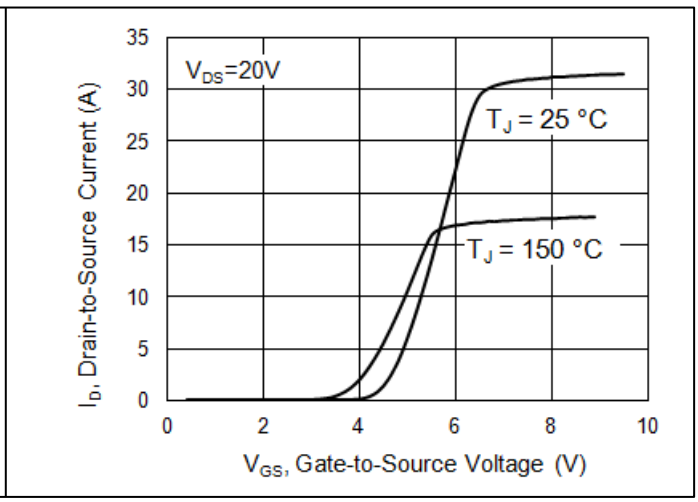


Fig 8 . Transfer characteristics

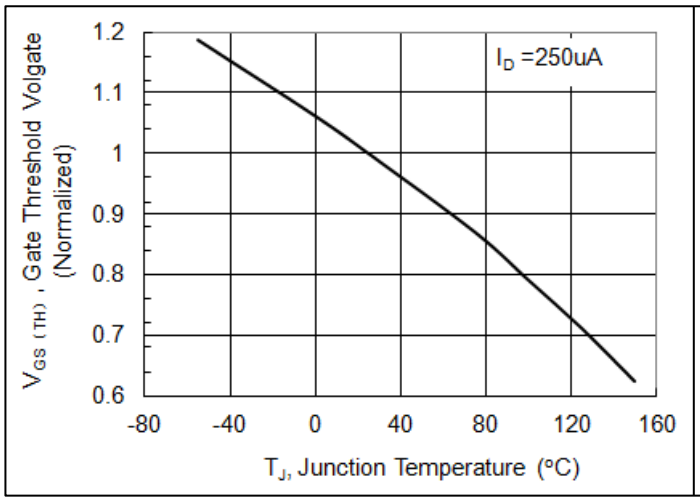


Fig 9 . $V_{GS(TH)}$ vs junction temperature

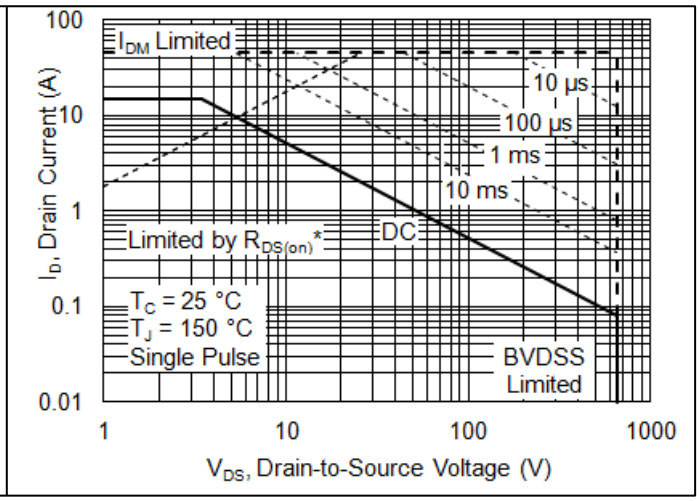


Fig 10. Safe operating area

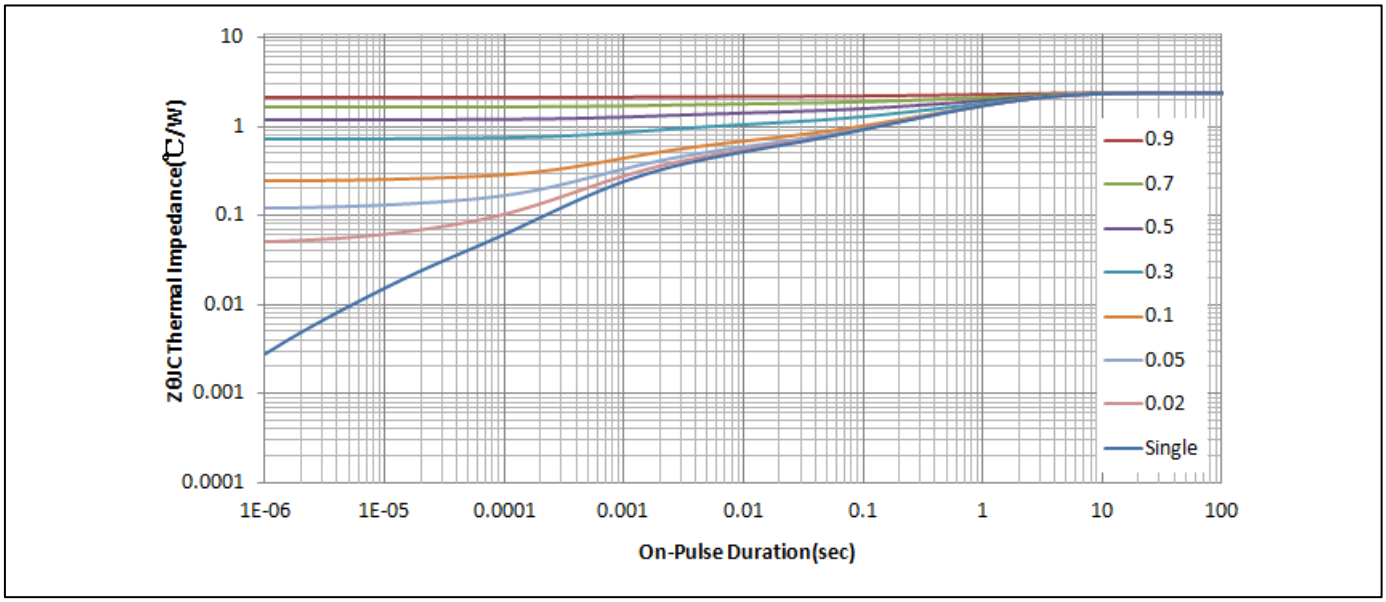
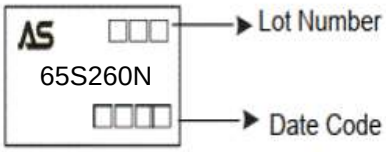


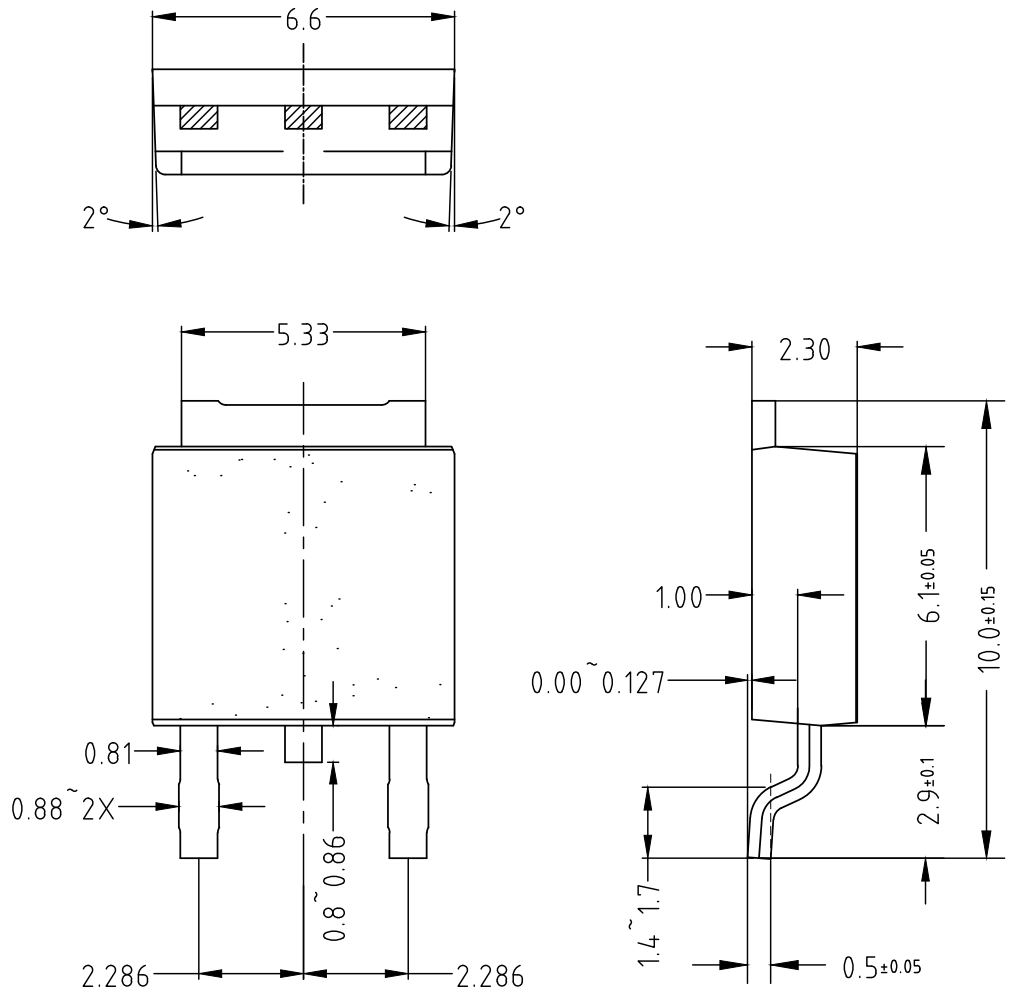
Fig 11. Transient thermal impedance

Ordering and Marking Information

Ordering Device No.	Marking	Package	Packing	Quantity
ASDM65S260NKQ-R	65S260N	TO-252	Tape&Reel	2500/Reel

PACKAGE	MARKING
TO-252	

TO-252


6.6
2°
2°
5.33
0.81
0.88~2X
0.8~0.86
2.286
2.286
2.30
1.00
0.00~0.127
6.1±0.05
10.0±0.15
2.9±0.1
1.4~1.7
0.5±0.05

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